



**Advanced Power
Electronics Corp.**

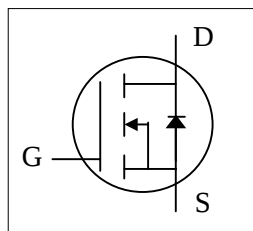
AP18T10GP

RoHS-compliant Product

N-CHANNEL ENHANCEMENT MODE

POWER MOSFET

- ▼ Simple Drive Requirement
- ▼ Lower Gate Charge
- ▼ Fast Switching Characteristic

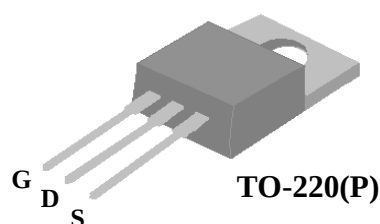


BV_{DSS}	100V
$R_{DS(ON)}$	160m Ω
I_D	9A

Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220 package is widely preferred for commercial-industrial power applications and suited for low voltage applications such as DC/DC converters.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	+20	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current, V_{GS} @ 10V	9	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current, V_{GS} @ 10V	5.6	A
I_{DM}	Pulsed Drain Current ¹	30	A
$P_D@T_C=25^{\circ}C$	Total Power Dissipation	28	W
$P_D@T_A=25^{\circ}C$	Total Power Dissipation	2	W
T_{STG}	Storage Temperature Range	-55 to 150	$^{\circ}C$
T_J	Operating Junction Temperature Range	-55 to 150	$^{\circ}C$

Thermal Data

Symbol	Parameter	Value	Units
R_{thj-c}	Maximum Thermal Resistance, Junction-case	4.5	$^{\circ}C/W$
R_{thj-a}	Maximum Thermal Resistance, Junction-ambient	62	$^{\circ}C/W$



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Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	100	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =5A	-	-	160	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	1	-	3	V
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =5A	-	5.6	-	S
I _{DSS}	Drain-Source Leakage Current	V _{DS} =80V, V _{GS} =0V	-	-	25	uA
	Drain-Source Leakage Current (T _j =125°C)	V _{DS} =80V, V _{GS} =0V	-	-	250	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Q _g	Total Gate Charge ²	I _D =5A	-	10	16	nC
Q _{gs}	Gate-Source Charge	V _{DS} =80V	-	2.5	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =10V	-	4.5	-	nC
t _{d(on)}	Turn-on Delay Time ²	V _{DS} =50V	-	6.5	-	ns
t _r	Rise Time	I _D =5A	-	10	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =3.3Ω	-	13	-	ns
t _f	Fall Time	V _{GS} =10V	-	3.4	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	425	680	pF
C _{oss}	Output Capacitance	V _{DS} =25V	-	55	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	33	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =5A, V _{GS} =0V	-	-	1.3	V
t _{rr}	Reverse Recovery Time ²	I _S =5A, V _{GS} =0V	-	53	-	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	130	-	nC

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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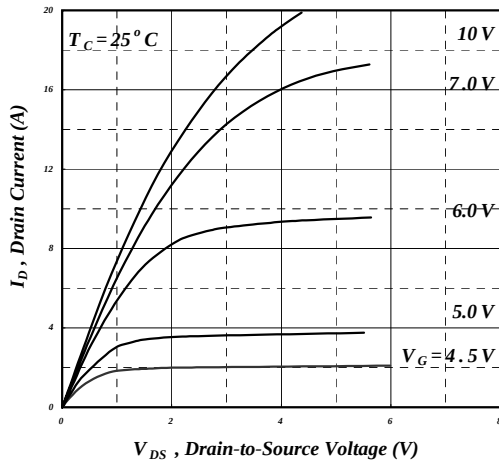


Fig 1. Typical Output Characteristics

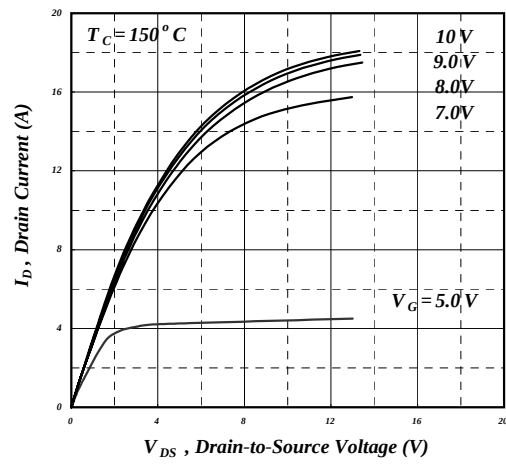


Fig 2. Typical Output Characteristics

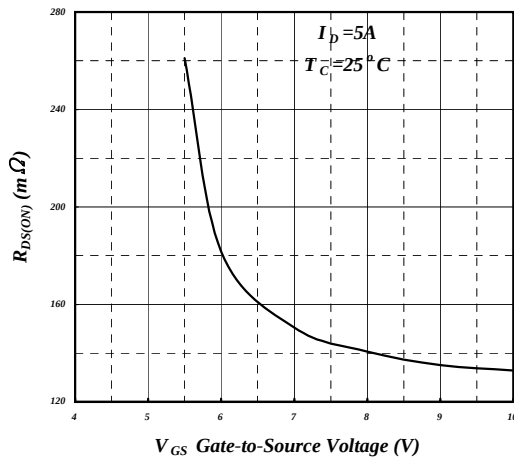


Fig 3. On-Resistance v.s. Gate Voltage

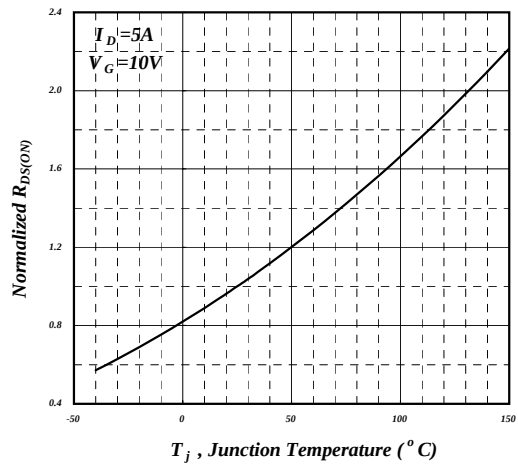


Fig 4. Normalized On-Resistance v.s. Junction Temperature

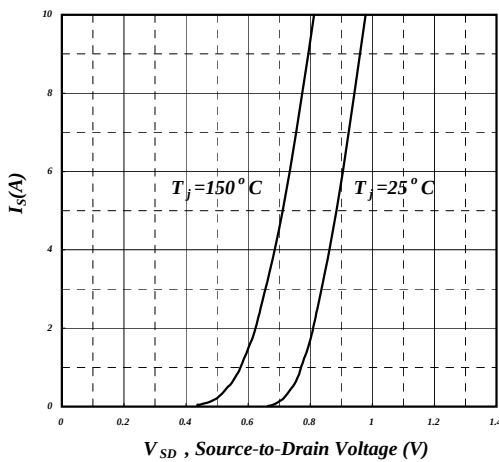


Fig 5. Forward Characteristic of Reverse Diode

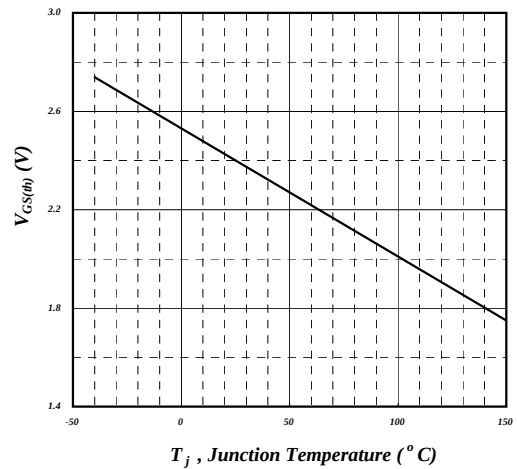


Fig 6. Gate Threshold Voltage v.s. Junction Temperature



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